The MPT Rapid Thermal Processor (RTP) is located in the Class-1000 cleanroom.

It uses high-intensity visible radiation (tungsten halogen lamps) to heat single wafers (up to 6 inch full wafers or chips) at a rate of 1-200°C per second for short periods of time (1-600 seconds) and hold at precisely controlled temperatures (400°C to 1200°C).

Air, Nitrogen, Forming Gas (5% H2 in N2), Oxygen, and Argon gases are used in the process chamber for polysilicon annealing, oxide reflow, contact alloying, and ion implant activation.